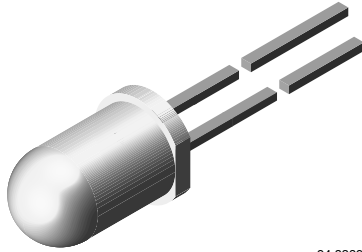




# High Power Infrared Emitting Diode, 940 nm, GaAlAs/GaAs



94 8389

### FEATURES

- Package type: leaded
- Package form: T-1¼
- Dimensions (in mm): Ø 5
- Peak wavelength:  $\lambda_p = 940$  nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity:  $\phi = \pm 25^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC



### DESCRIPTION

TSAL6400 is an infrared, 940 nm emitting diode in GaAlAs/GaAs technology with high radiant power molded in a blue-gray plastic package.

### Note

\*\* Please see document "Vishay Material Category Policy": [www.vishay.com/doc?99902](http://www.vishay.com/doc?99902)

### APPLICATIONS

- Infrared remote control units with high power requirements
- Free air transmission systems
- Infrared source for optical counters and card readers

| PRODUCT SUMMARY |                        |         |                     |                     |
|-----------------|------------------------|---------|---------------------|---------------------|
| COMPONENT       | I <sub>e</sub> (mW/sr) | φ (deg) | λ <sub>p</sub> (nm) | t <sub>r</sub> (ns) |
| TSAL6400        | 40                     | ± 25    | 940                 | 800                 |

### Note

- Test conditions see table "Basic Characteristics"

| ORDERING INFORMATION |           |                              |              |
|----------------------|-----------|------------------------------|--------------|
| ORDERING CODE        | PACKAGING | REMARKS                      | PACKAGE FORM |
| TSAL6400             | Bulk      | MOQ: 4000 pcs, 4000 pcs/bulk | T-1¼         |

### Note

- MOQ: minimum order quantity

| ABSOLUTE MAXIMUM RATINGS (T <sub>amb</sub> = 25 °C, unless otherwise specified) |  |                   |               |      |
|---|--|-------------------|---------------|------|
| PARAMETER   | TEST CONDITION                                   | SYMBOL            | VALUE         | UNIT |
| Reverse voltage   |  | V <sub>R</sub>    | 5             | V    |
| Forward current   |  | I <sub>F</sub>    | 100           | mA   |
| Peak forward current  | t <sub>p</sub> /T = 0.5, t <sub>p</sub> = 100 μs | I <sub>FM</sub>   | 200           | mA   |
| Surge forward current   | t <sub>p</sub> = 100 μs                          | I <sub>FSM</sub>  | 1.5           | A    |
| Power dissipation   |  | P <sub>V</sub>    | 160           | mW   |
| Junction temperature  |  | T <sub>j</sub>    | 100           | °C   |
| Operating temperature range   |  | T <sub>amb</sub>  | - 40 to + 85  | °C   |
| Storage temperature range   |  | T <sub>stg</sub>  | - 40 to + 100 | °C   |
| Soldering temperature   | t ≤ 5 s, 2 mm from case                          | T <sub>sd</sub>   | 260           | °C   |
| Thermal resistance junction/ambient   | J-STD-051, leads 7 mm soldered on PCB            | R <sub>thJA</sub> | 230           | K/W  |

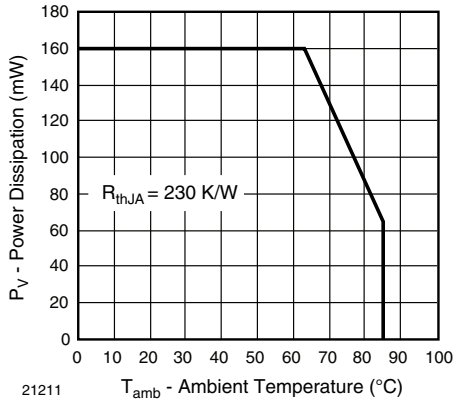


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

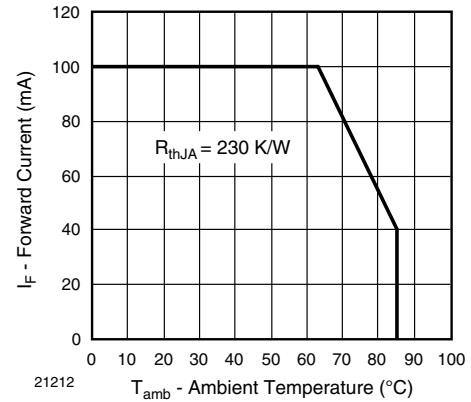


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| <b>BASIC CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified) |   |                             |      |       |      |       |
|---|---|-----------------------------|------|-------|------|-------|
| PARAMETER   | TEST CONDITION                                  | SYMBOL                      | MIN. | TYP.  | MAX. | UNIT  |
| Forward voltage   | I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms | V <sub>F</sub>              |      | 1.35  | 1.6  | V     |
|   | I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs   | V <sub>F</sub>              |      | 2.6   | 3    | V     |
| Temperature coefficient of V <sub>F</sub>   | I <sub>F</sub> = 1 mA                           | TK <sub>V<sub>F</sub></sub> |      | - 1.8 |      | mV/K  |
| Reverse current   | V <sub>R</sub> = 5 V                            | I <sub>R</sub>              |      |       | 10   | μA    |
| Junction capacitance  | V <sub>R</sub> = 0 V, f = 1 MHz, E = 0          | C <sub>j</sub>              |      | 25    |      | pF    |
| Radiant intensity   | I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms | I <sub>e</sub>              | 25   | 40    | 125  | mW/sr |
|   | I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs   | I <sub>e</sub>              | 220  | 310   |      | mW/sr |
| Radiant power   | I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms | φ <sub>e</sub>              |      | 35    |      | mW    |
| Temperature coefficient of φ <sub>e</sub>   | I <sub>F</sub> = 20 mA                          | TK <sub>φ<sub>e</sub></sub> |      | - 0.6 |      | %/K   |
| Angle of half intensity   |   | φ                           |      | ± 25  |      | deg   |
| Peak wavelength   | I <sub>F</sub> = 100 mA                         | λ <sub>p</sub>              |      | 940   |      | nm    |
| Spectral bandwidth  | I <sub>F</sub> = 100 mA                         | Δλ                          |      | 50    |      | nm    |
| Temperature coefficient of λ <sub>p</sub>   | I <sub>F</sub> = 100 mA                         | TK <sub>λ<sub>p</sub></sub> |      | 0.2   |      | nm/K  |
| Rise time   | I <sub>F</sub> = 100 mA                         | t <sub>r</sub>              |      | 800   |      | ns    |
| Fall time   | I <sub>F</sub> = 100 mA                         | t <sub>f</sub>              |      | 800   |      | ns    |
| Virtual source diameter   | Method: 63 % encircled energy                   | d                           |      | 2.2   |      | mm    |

**BASIC CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)

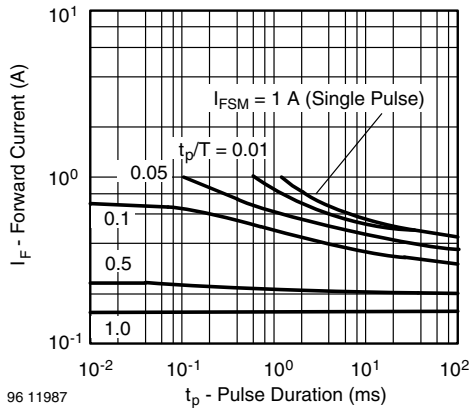


Fig. 3 - Pulse Forward Current vs. Pulse Duration

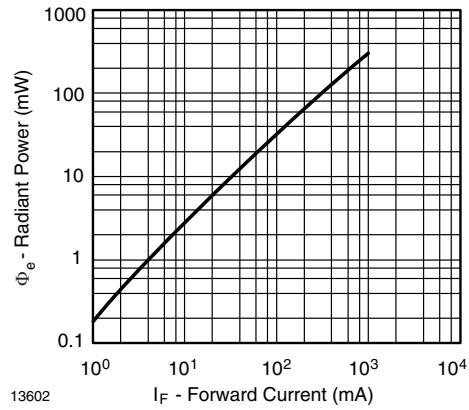


Fig. 6 - Radiant Power vs. Forward Current

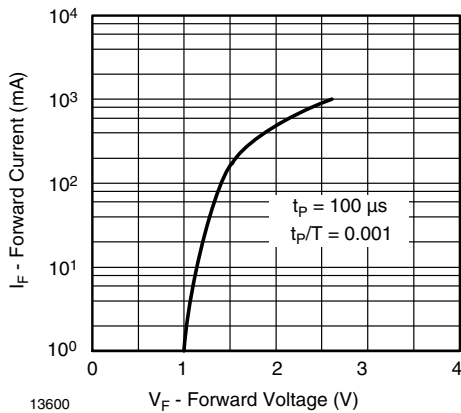


Fig. 4 - Forward Current vs. Forward Voltage

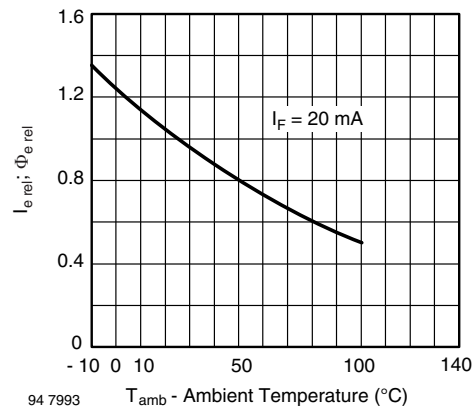


Fig. 7 - Relative Radiant Intensity/Power vs. Ambient Temperature

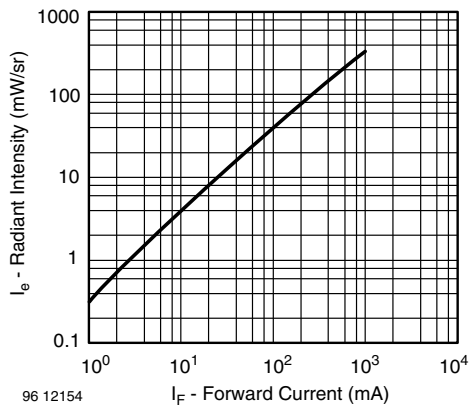


Fig. 5 - Radiant Intensity vs. Forward Current

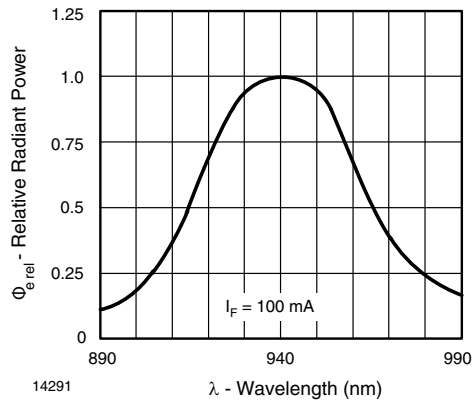
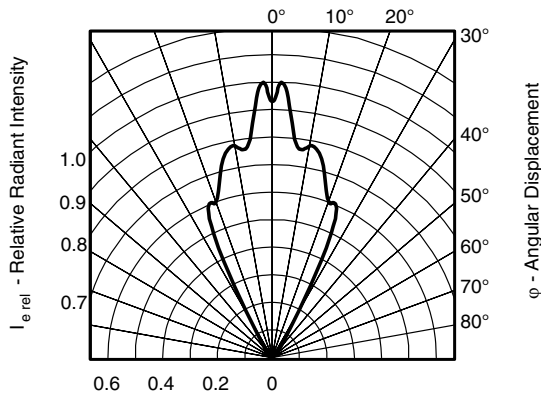


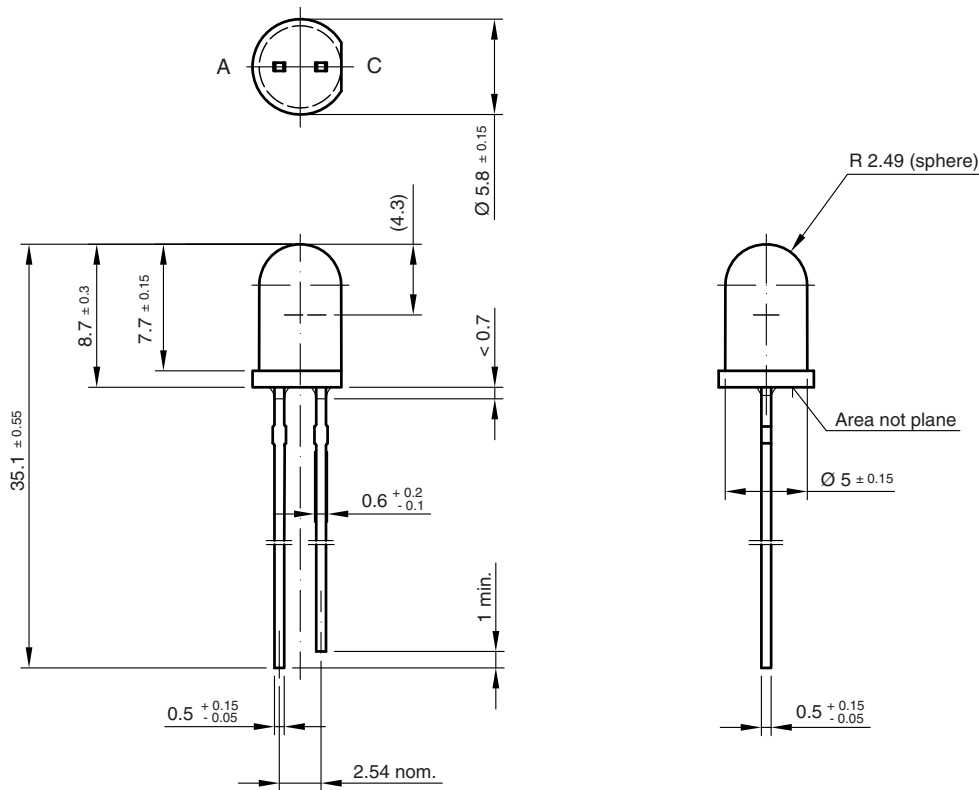
Fig. 8 - Relative Radiant Power vs. Wavelength



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Fig. 9 - Relative Radiant Intensity vs. Angular Displacement

**PACKAGE DIMENSIONS** in millimeters



Drawing-No.: 6.544-5259.07-4

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### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

Skype отдела продаж:

moschip.ru

moschip.ru\_4

moschip.ru\_6

moschip.ru\_9